

### AMENDMENT TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application. New claim 6 is being added, and claims 1 and 6 are the independent claims in the case.

#### LISTING OF CLAIMS:

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1. (Currently Amended) A method of creating a stack of integrated circuits selectively connected to provide increased memory density in an application, the method comprising the steps of:

C<sup>2</sup> providing a carrier frame configured to have a plurality of members emergent into a window within the carrier frame;

applying a first portion of a solder-containing compound to the first side of the plurality of members;

after applying said first portion of solder-containing compound, placing a first packaged integrated circuit in contact with the plurality of members;

processing the first integrated circuit and the carrier frame with a heat source to create a first set of solder connections between the plurality of members and the first packaged integrated circuit;

after said processing step, applying a second portion of a solder-containing compound to the second side of the plurality of members of the carrier frame;

after applying the second portion of solder-containing compound, placing a second packaged integrated circuit in contact with the plurality of members; and

processing the second integrated circuit and the carrier frame with a heat source to create a second set of solder connections between the plurality of members and the second integrated circuit.

2. (Currently Amended) The method of claim 1 in which ~~plural iterations of the carrier frame are created in~~ the carrier frame is provided from a carrier bed having a plurality of carrier frames.

C2  
(contd)  
3. (Previously Presented). The method of claim 1 in which the carrier frame and the first and second integrated circuits are further processed by separation of the plurality of members from the carrier frame.

4. (Cancelled).

5. (Cancelled).

6. (New) A method of creating a stack of integrated circuits selectively connected to provide increased memory density in an application, the method comprising the steps of:

providing a carrier frame configured to have a plurality of members emergent into a window within the carrier frame;

applying a first portion of a solder-containing compound to the first side of the plurality of members;

placing a first packaged integrated circuit having external leads extending away from the packaged integrated circuit in contact with the plurality of members;

processing the first integrated circuit and the carrier frame with a heat source to create a first set of solder connections between the plurality of members and a plurality of the external, extending away, leads of the first packaged integrated circuit;

*C2  
(concl.)*  
applying a second portion of a solder-containing compound to the second side of the plurality of members of the carrier frame;

placing a second packaged integrated circuit having external leads extending away from the second packaged integrated circuit in contact with the plurality of members; and

processing the second integrated circuit and the carrier frame with a heat source to create a second set of solder connections between the plurality of members and a plurality of the external, extending away, leads of the second integrated circuit.

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